



BRP100N220P6

N-channel Enhancement Mode Power MOSFET

芯天下技术股份有限公司

XTX Technology Inc.

Tel: (+86 755) 28229862

Fax: (+86 755) 28229847

Web Site: <http://www.xtxtech.com/>

Technical Contact: fae@xtxtech.com

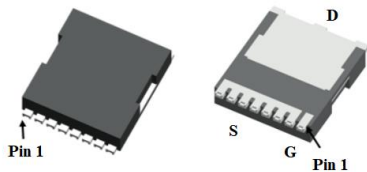
* Information furnished is believed to be accurate and reliable. However, XTX Technology Inc. assumes no responsibility for the consequences of use of such information or for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent rights of XTX Technology Inc. Specifications mentioned in this publication are subjected to change without notice. This publication supersedes and replaces all information previously supplied. XTX Technology Inc. products are not authorized for use as critical components in life support devices or systems without express written approval of XTX Technology Inc. The XTX logo is a registered trademark of XTX Technology Inc. All other names are the property of their respective own.

FEATURES

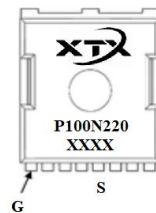
- ◆ 100V, 220A
- ◆ $R_{DS(ON)} < 1.45m\Omega @ V_{GS} = 10V$
- ◆ Ultra-low $R_{DS(ON)}$
- ◆ Low Gate Charge
- ◆ Lead Free

APPLICATIONS

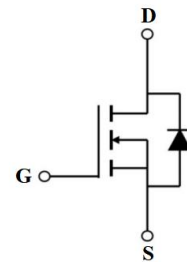
- ◆ Motor Driving in Power Tool, E-vehicle, Robotics
- ◆ Current Switching in DC/DC & AC/DC
- ◆ Power Management



TOLL-8



Marking and Pin Assignment



Schematic Diagram

PACKAGE MARKING AND ORDERING INFORMATION

OPN	Marking	Package	Quantity
BRP100N220P6	P100N220 XXXX	TOLL-8	2000pcs/Reel

ABSOLUTE MAXIMUM RATINGS

Symbol	Definition		Ratings	Unit
V_{DS}	Drain-to-Source Voltage		100	V
V_{GS}	Gate-to-Source Voltage		± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ C$	220	A
		$T_C = 100^\circ C$	146	A
I_{DM}	Pulsed Drain Current ⁽¹⁾		880	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾		648	mJ
P_D	Power Dissipation, $T_C = 25^\circ C$		500	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		0.25	$^\circ C/W$
T_J, T_{STG}	Junction & Storage Temperature Range		-55 ~ +150	$^\circ C$

ELECTRICAL CHARACTERISTICS (All test condition is $T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = 250μA, V _{GS} = 0V	100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 80V, V _{GS} = 0V	-	-	1	uA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250uA	2.0	3.0	4.0	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽³⁾	V _{GS} = 10V, I _D = 30A	-	1.2	1.45	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 50V, f = 1MHz	-	13258	-	pF
C _{oss}	Output Capacitance		-	2058	-	pF
C _{rss}	Reverse Transfer Capacitance		-	111	-	pF
R _g	Gate Resistance	V _{GS} = 0V, V _{DS} = 0V, f = 1MHz	-	3.6	-	Ω
Q _g	Total Gate Charge	V _{GS} = 0 to 10V V _{DS} = 50V, I _D = 30A	-	240	-	nC
Q _{gs}	Gate Source Charge		-	60	-	nC
Q _{gd}	Gate Drain("Miller") Charge		-	59	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{GS} = 10V, V _{DS} = 50V I _D = 30A, R _{GEN} = 4.5Ω	-	33	-	ns
t _r	Turn-On Rise Time		-	69	-	ns
t _{d(off)}	Turn-Off Delay Time		-	172	-	ns
t _f	Turn-Off Fall Time		-	105	-	ns
Drain-Source Diode Characteristics						
I _S	Continuous Source Current		-	-	220	A
V _{SD}	Forward on voltage	V _{GS} = 0V, I _S = 30A	-	-	1.3	V
T _{rr}	Reverse Recovery Time	I _F = 30A, di/dt = 100A/us	-	124	-	ns
Q _{rr}	Reverse Recovery Charge		-	388	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting $T_J=25^{\circ}\text{C}$, $V_{DD}=50\text{V}$, $V_G=10\text{V}$, $L=0.5\text{mH}$, $I_{AS}=50\text{A}$
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

TYPICAL PERFORMANCE CHARACTERISTICS

Fig. 1 - Typical Output Characteristics

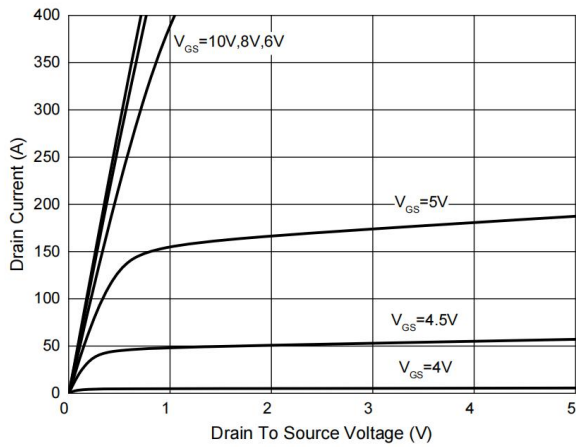


Fig. 2 - Transfer Characteristics

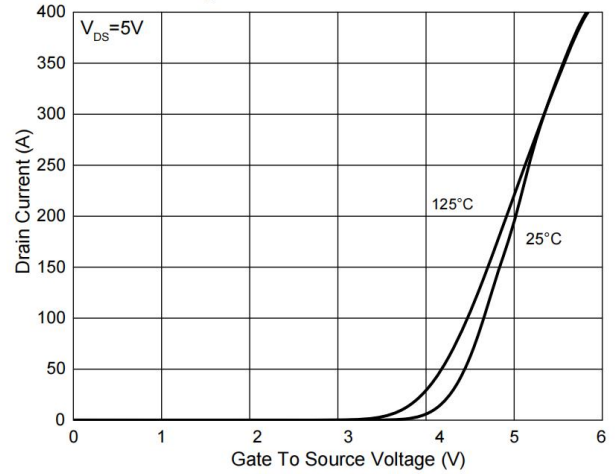


Fig. 3 - $R_{DS(ON)}-V_{GS}$

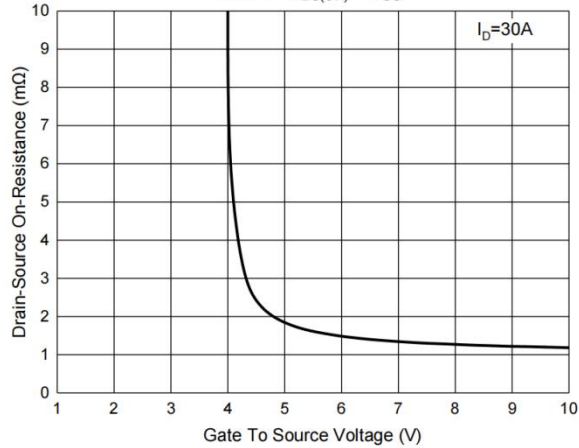


Fig. 4 - $R_{DS(ON)}-I_D$

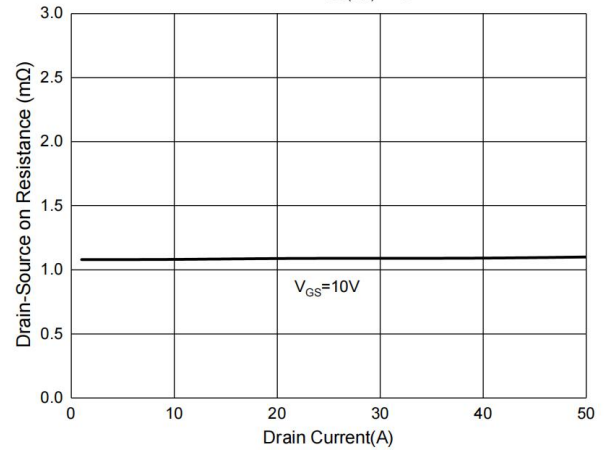


Fig. 5 - Capacitance Characteristics

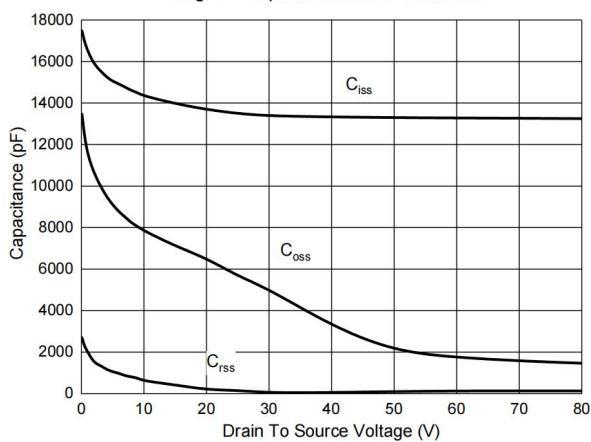
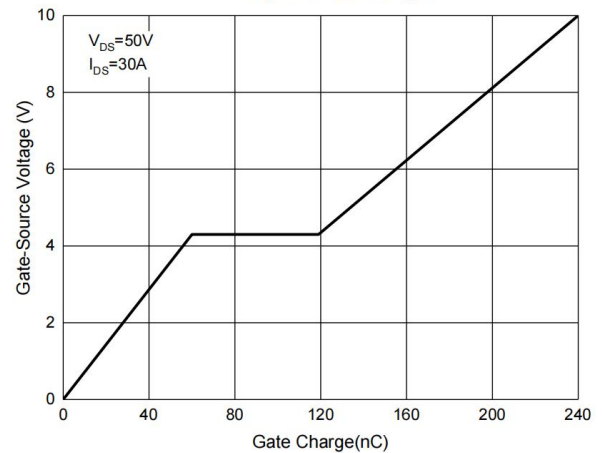


Fig. 6 - Gate Charge



TYPICAL PERFORMANCE CHARACTERISTICS

Fig. 7 - Normalized Threshold Voltage

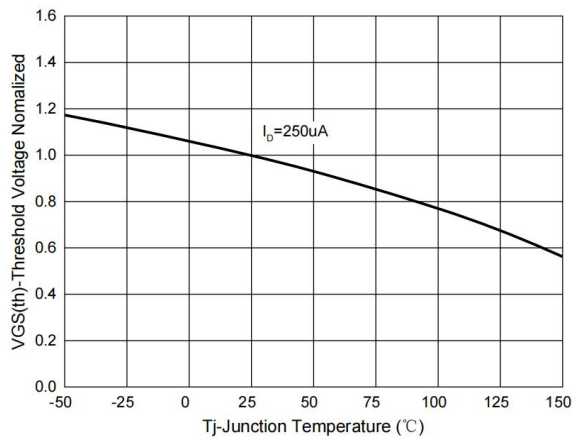


Fig. 8 - Normalized On Resistance Characteristics

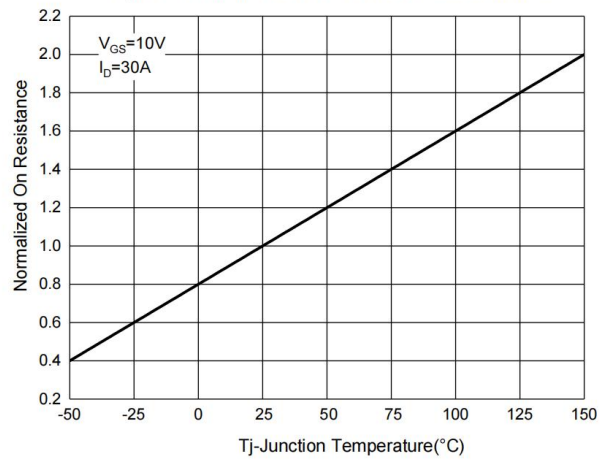


Fig. 9 - $I_S - V_{SD}$

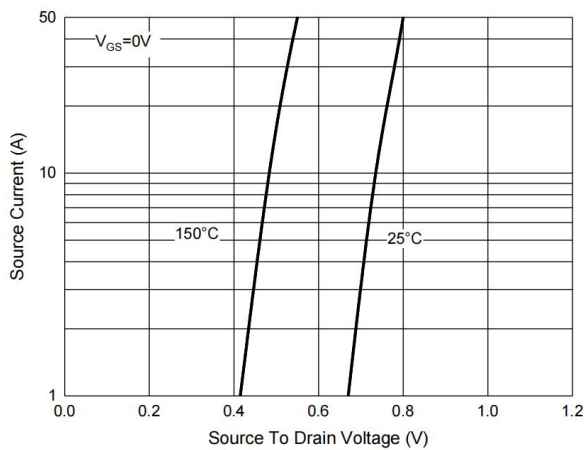


Fig. 10 - Drain Current

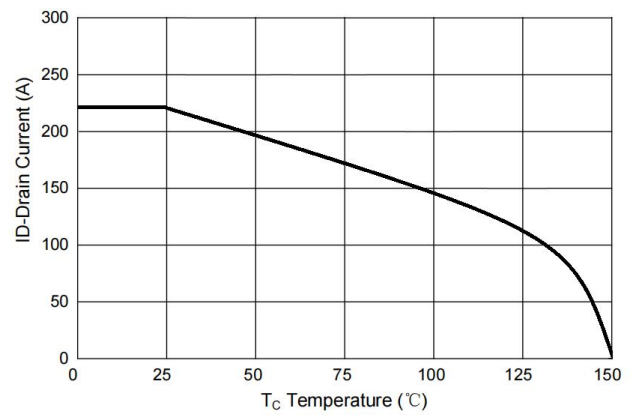


Fig. 11 - PD Dissipation

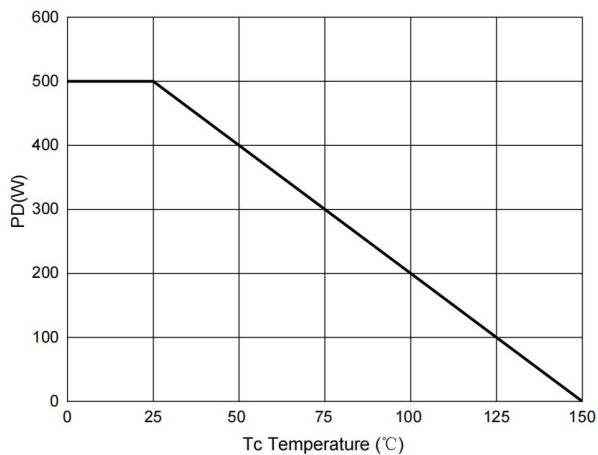
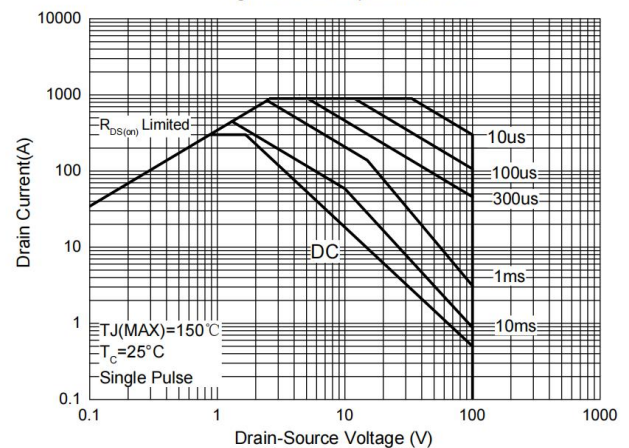
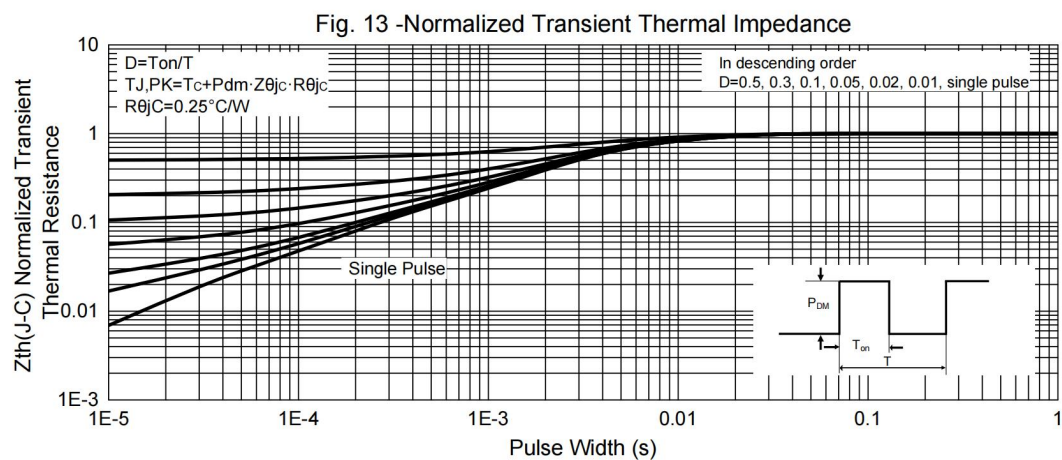


Fig. 12 - Safe Operation Area



TYPICAL PERFORMANCE CHARACTERISTICS



TEST CIRCUIT

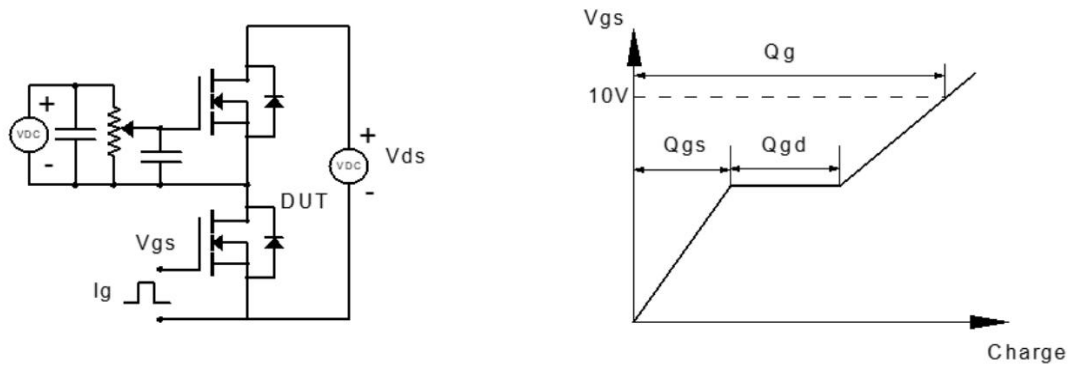


Figure 14: Gate Charge Test Circuit & Waveform

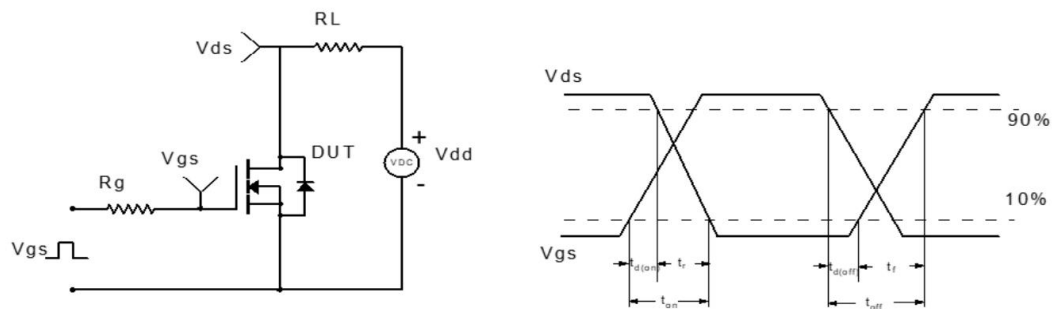


Figure 15: Resistive Switching Test Circuit & Waveform

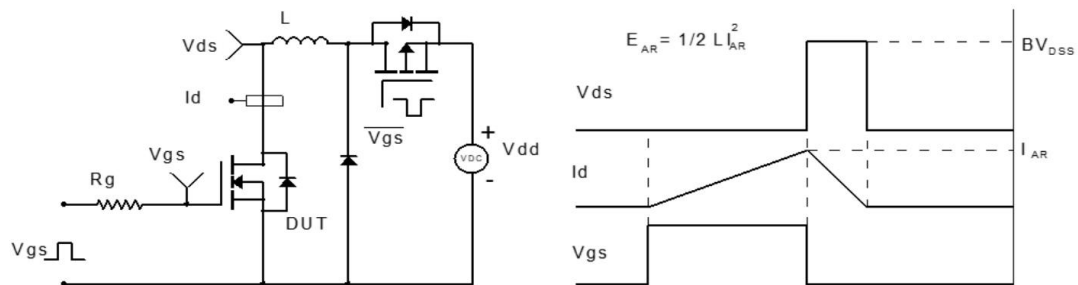


Figure 16: Unclamped Inductive Switching Test Circuit & Waveform

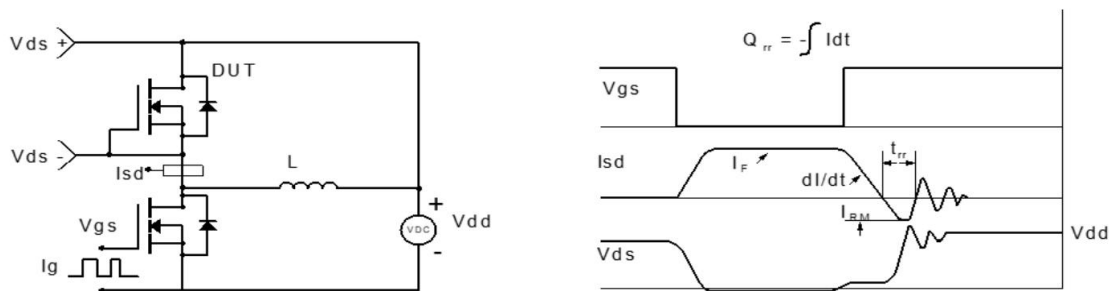
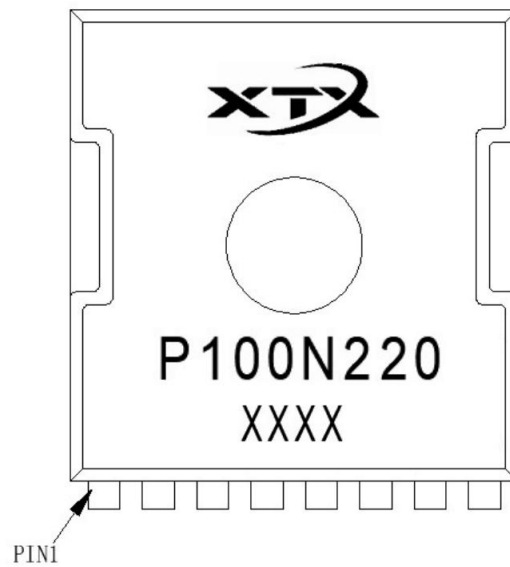


Figure 17: Diode Recovery Test Circuit & Waveform

MARKING INFORMATION



1st Line: XTX Logo

2nd Line: Part Number (P100N220)

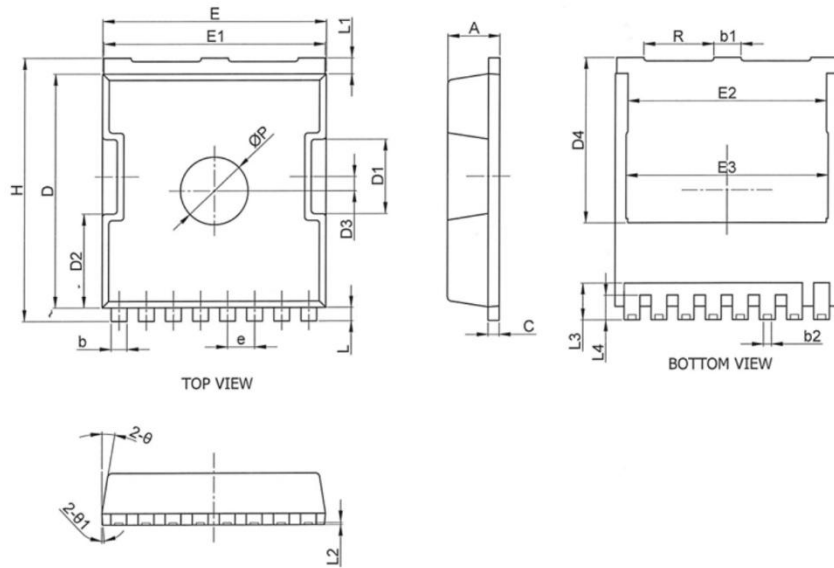
3rd Line: Date Code (XXXX)

XX: Year

XX: Week (01 to 53)

Year	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	21	22	23	24	25	26	27	28	29	30	31	32	33

DETAIL PACKAGE OUTLINE DRAWING (TOLL-8)



SYMBOL	MILLIMETERS		
	MIN	NOM	MAX
A	2.20	2.30	2.40
b	0.60	0.70	0.80
b1	1.10	1.20	1.30
b2	0.26	0.36	0.51
C	0.40	0.50	0.60
D	10.30	10.40	10.50
D1	3.20	3.30	3.40
D2	4.08	4.18	4.28
D3	0.53	0.63	0.73
D4	7.25	7.35	7.50
E	9.80	9.90	10.00
E1	9.70	9.80	9.90
E2	8.70	8.80	8.90
E3	8.85	8.95	9.05
e	1.20 BSC		
H	11.50	11.70	11.90
L	0.50	0.60	0.70
L1	0.60	0.70	0.80
L2	0.05	0.10	0.20
L3	1.45	1.65	1.85
L4	0.90	1.10	1.30
P	2.00	3.00	4.00
R	3.00	3.10	3.20
θ	7°	9°	11°
θ1	3°	5°	7°

REVISION HISTORY

Number	Description
Rev 1.0	BRP100N220P6 datasheet release